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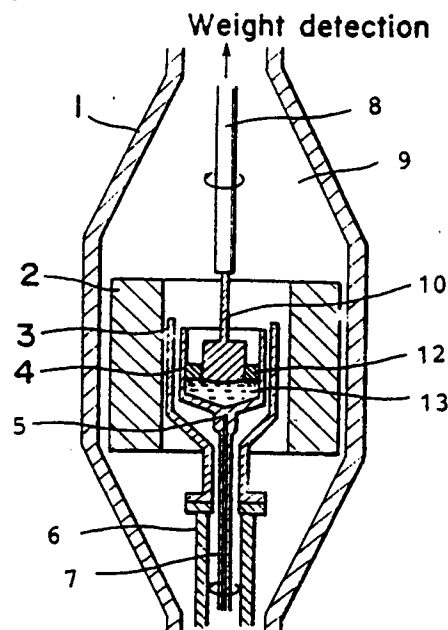
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(54) **Method of growing single crystal of compound semiconductors.**

(57) A method of growing single crystal is provided, wherein, upon growing a single crystal of compound semiconductors, in particular, single crystal of InP by flat top shape, the crystal is pulled up after the temperature drop of the melt (13) has almost stopped and further at the point of time when the meniscus at the interface of solid-liquid can be seen over the whole circumference of the surface of the melt, for the purpose of pulling up the single crystal without forming a facet at the shoulder portion of the crystal. The invention achieves greatly decreased generation probability of twin crystals and a drastically improved retention of single-crystallization.

Fig. 2**EP 0 476 389 A3**



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EUROPEAN SEARCH REPORT

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EP 91 11 4547

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl.5)
P,X	JOURNAL OF CRYSTAL GROWTH. vol. 113, no. 1/2, August 1991, AMSTERDAM NL pages 221 - 226 YOSHIDA ET AL 'InP single crystal growth with controlled supercooling during the early stage by a modified LEC method' * the whole document *	1,5	C30B15/00 C30B29/40
A	US-A-4 299 651 (BONNER) * claim 1 *	1	
A	PATENT ABSTRACTS OF JAPAN vol. 10, no. 296 (C-377)(2352) 8 October 1986 & JP-A-61 111 991 (HITACHI CABLE LTD) 30 May 1986 * abstract *		
A	MATERIALS LETTERS vol. 8, no. 11, November 1989, AMSTERDAM NL pages 486 - 488 AHERN ET AL 'magnetically stabilized kryoppoulos growth of undoped InP' * page 487 *	1	
			TECHNICAL FIELDS SEARCHED (Int. Cl.5)
			C30B
The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 24 MARCH 1993	Examiner COOK S.D.
CATEGORY OF CITED DOCUMENTS			
X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document		T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document	